

Silicon Z-Diodes

Features

- Very sharp reverse characteristic
- Very high stability
- Low reverse current level
- V_Z -tolerance $\pm 5\%$



94 9367

Applications

Voltage stabilization

Absolute Maximum Ratings

 $T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Power dissipation	$T_L \leq 75^\circ\text{C}$		P_V	500	mW
Z-current			I_Z	P_V/V_Z	mA
Junction temperature			T_j	200	$^\circ\text{C}$
Storage temperature range			T_{stg}	-65...+200	$^\circ\text{C}$

Maximum Thermal Resistance

 $T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	$l=9.5\text{mm (3/8")}$, $T_L=\text{constant}$	R_{thJA}	300	K/W

Electrical Characteristics

 $T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=200\text{mA}$		V_F			1.1	V

1N5221B...1N5267B



Vishay Telefunken

Type	$V_{Znom}^{1)}$	I_{ZT}	for	r_{zIT}	r_{zik}	at	I_{ZK}	I_R	at	V_R	TK_{VZ}
	V	mA		Ω	Ω		mA	μA		V	%/K
1N5221B	2.4	20		< 30	< 1200		0.25	< 100		1.0	< -0.085
1N5222B	2.5	20		< 30	< 1250		0.25	< 100		1.0	< -0.085
1N5223B	2.7	20		< 30	< 1300		0.25	< 75		1.0	< -0.080
1N5224B	2.8	20		< 30	< 1400		0.25	< 75		1.0	< -0.080
1N5225B	3.0	20		< 29	< 1600		0.25	< 50		1.0	< -0.075
1N5226B	3.3	20		< 28	< 1600		0.25	< 25		1.0	< -0.070
1N5227B	3.6	20		< 24	< 1700		0.25	< 15		1.0	< -0.065
1N5228B	3.9	20		< 23	< 1900		0.25	< 10		1.0	< -0.060
1N5229B	4.3	20		< 22	< 2000		0.25	< 5		1.0	< +0.055
1N5230B	4.7	20		< 19	< 1900		0.25	< 5		2.0	< +0.030
1N5231B	5.1	20		< 17	< 1600		0.25	< 5		2.0	< +0.030
1N5232B	5.6	20		< 11	< 1600		0.25	< 5		3.0	< +0.038
1N5233B	6.0	20		< 7	< 1600		0.25	< 5		3.5	< +0.038
1N5234B	6.2	20		< 7	< 1000		0.25	< 5		4.0	< +0.045
1N5235B	6.8	20		< 5	< 750		0.25	< 3		5.0	< +0.050
1N5236B	7.5	20		< 6	< 500		0.25	< 3		6.0	< +0.058
1N5237B	8.2	20		< 8	< 500		0.25	< 3		6.5	< +0.062
1N5238B	8.7	20		< 8	< 600		0.25	< 3		6.5	< +0.065
1N5239B	9.1	20		< 10	< 600		0.25	< 3		7.0	< +0.068
1N5240B	10	20		< 17	< 600		0.25	< 3		8.0	< +0.075
1N5241B	11	20		< 22	< 600		0.25	< 2		8.4	< +0.076
1N5242B	12	20		< 30	< 600		0.25	< 1		9.1	< +0.077
1N5243B	13	9.5		< 13	< 600		0.25	< 0.5		9.9	< +0.079
1N5244B	14	9.0		< 15	< 600		0.25	< 0.1		10	< +0.082
1N5245B	15	8.5		< 16	< 600		0.25	< 0.1		11	< +0.082
1N5246B	16	7.8		< 17	< 600		0.25	< 0.1		12	< +0.083
1N5247B	17	7.4		< 19	< 600		0.25	< 0.1		13	< +0.084
1N5248B	18	7.0		< 21	< 600		0.25	< 0.1		14	< +0.085
1N5249B	19	6.6		< 23	< 600		0.25	< 0.1		14	< +0.086
1N5250B	20	6.2		< 25	< 600		0.25	< 0.1		15	< +0.086
1N5251B	22	5.6		< 29	< 600		0.25	< 0.1		17	< +0.087
1N5252B	24	5.2		< 33	< 600		0.25	< 0.1		18	< +0.088
1N5253B	25	5.0		< 35	< 600		0.25	< 0.1		19	< +0.089
1N5254B	27	4.6		< 41	< 600		0.25	< 0.1		21	< +0.090
1N5255B	28	4.5		< 44	< 600		0.25	< 0.1		21	< +0.091
1N5256B	30	4.2		< 49	< 600		0.25	< 0.1		23	< +0.091
1N5257B	33	3.8		< 58	< 700		0.25	< 0.1		25	< +0.092
1N5258B	36	3.4		< 70	< 700		0.25	< 0.1		27	< +0.093
1N5259B	39	3.2		< 80	< 800		0.25	< 0.1		30	< +0.094
1N5260B	43	3.0		< 93	< 900		0.25	< 0.1		33	< +0.095
1N5261B	47	2.7		< 105	< 1000		0.25	< 0.1		36	< +0.095
1N5262B	51	2.5		< 125	< 1100		0.25	< 0.1		39	< +0.096
1N5263B	56	2.2		< 150	< 1300		0.25	< 0.1		43	< +0.096
1N5264B	60	2.1		< 170	< 1400		0.25	< 0.1		46	< +0.097
1N5265B	62	2.0		< 185	< 1400		0.25	< 0.1		47	< +0.097
1N5266B	68	1.8		< 230	< 1600		0.25	< 0.1		52	< +0.097
1N5267B	75	1.7		< 270	< 1700		0.25	< 0.1		56	< +0.098

¹⁾ Based on dc-measurement at thermal equilibrium; lead length = 9.5mm (3/8"); thermal resistance of heat sink = 30K/W

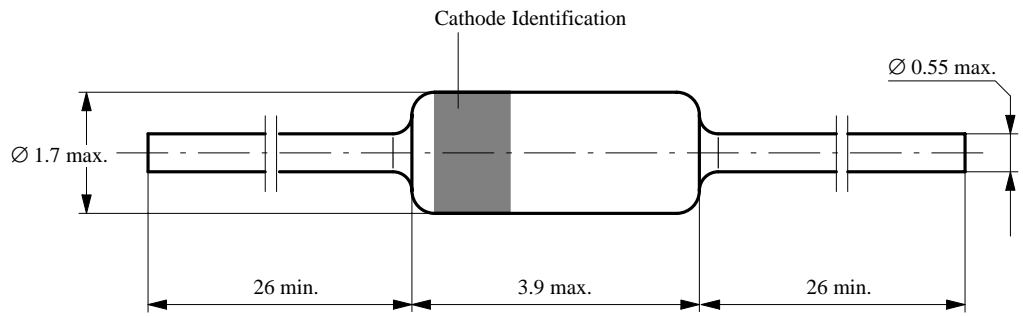
Dimensions in mm



technical drawings
according to DIN
specifications

94 9366

Standard Glass Case
54 A 2 DIN 41880
JEDEC DO 35
Weight max. 0.3 g





Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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